

Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$



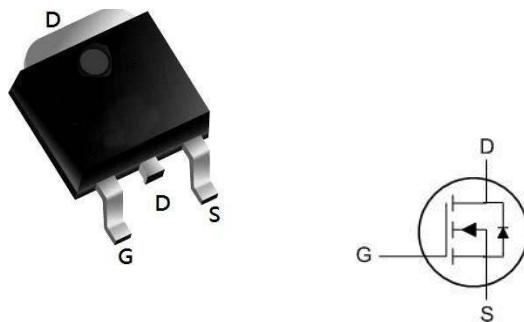
Product Summary

BVDSS	RDS(on)	ID
60V	4mΩ	120A

Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

TO252 Pin Configuration



Absolute Maximum Ratings:

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current T _c =25°C	I_D	120	A
T _c =100°C		57	
Pulsed Drain Current ¹	I_{DM}	360	A
Single Pulse Avalanche Energy ²	E_{AS}	135.2	mJ
Total Power Dissipation T _c =25°C	P_D	71.4	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	R_{JA}	58	°C/W
Thermal Resistance from Junction-to-Case	R_{JC}	1.75	°C/W

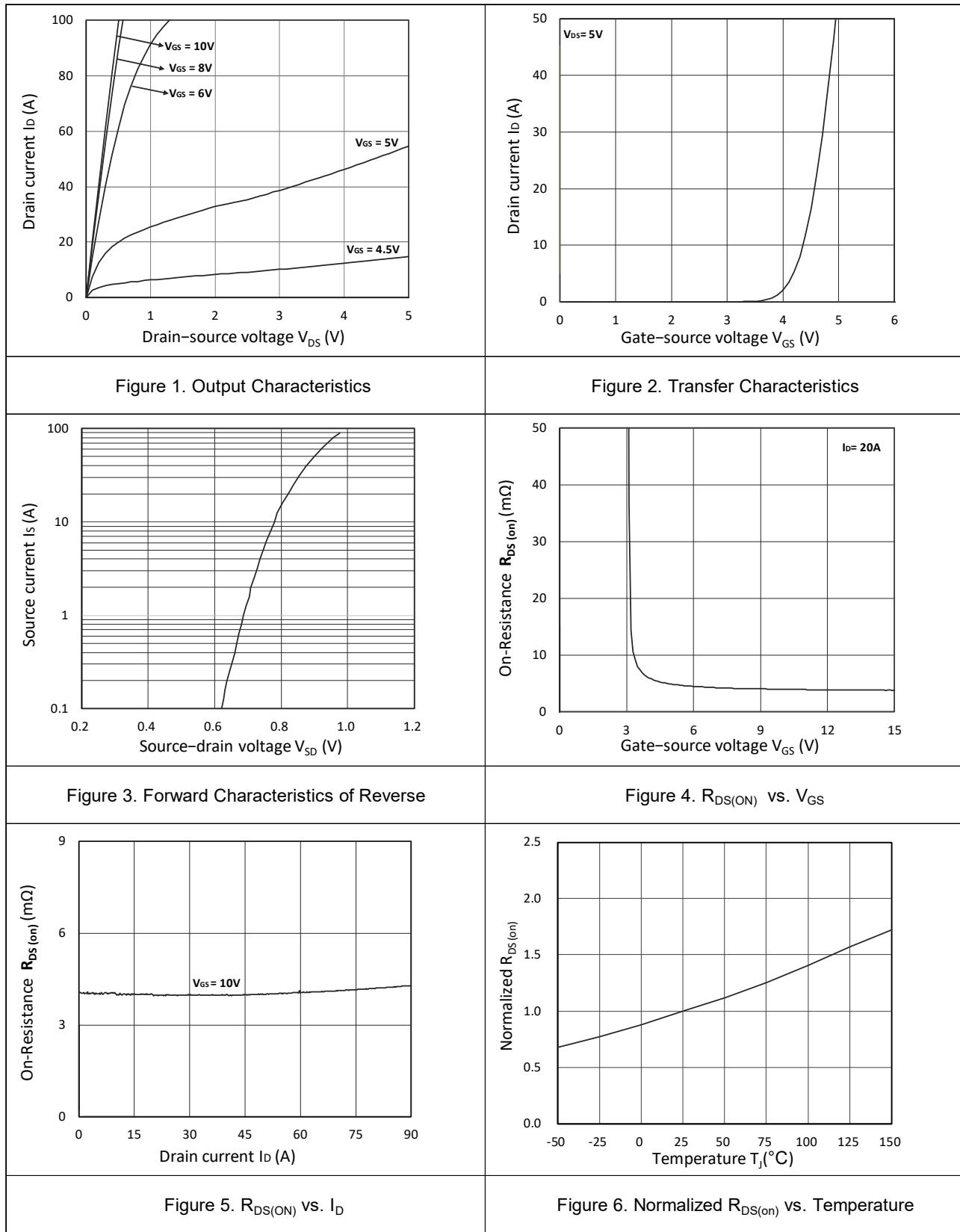
Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	60	-	-	V
Gate-body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current $T_J=25^\circ\text{C}$	I_{DSS}	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA
			-	-	100	
Gate-Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	2.9	3.5	V
Drain-Source On-Resistance ⁴	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	-	4	5.2	$\text{m}\Omega$
Forward Transconductance ⁴	g_{fs}	$V_{DS} = 10\text{V}, I_D = 20\text{A}$	-	89	-	S
Dynamic Characteristics⁵						
Input Capacitance	C_{iss}	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	-	1673	-	pF
Output Capacitance	C_{oss}		-	773	-	
Reverse Transfer Capacitance	C_{rss}		-	46.8	-	
Gate Resistance	R_g	$f = 1\text{MHz}$	-	1.8	-	Ω
Switching Characteristics⁵						
Total Gate Charge	Q_g	$V_{GS} = 10\text{V}, V_{DS} = 30\text{V}, I_D = 20\text{A}$	-	28.5	-	nC
Gate-Source Charge	Q_{gs}		-	7.8	-	
Gate-Drain Charge	Q_{gd}		-	8.4	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{V}, V_{DD} = 30\text{V}, R_G = 3\Omega, I_D = 20\text{A}$	-	11.2	-	ns
Rise Time	t_r		-	8.2	-	
Turn-Off Delay Time	$t_{d(off)}$		-	19.6	-	
Fall Time	t_f		-	6.2	-	
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{A}, dI/dt = 100\text{A}/\mu\text{s}$	-	50	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	20	-	nC
Drain-Source Body Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$I_S = 20\text{A}, V_{GS} = 0\text{V}$	-	-	1.2	V
Continuous Source Current	$T_c = 25^\circ\text{C}$	I_S	-	-	120	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})} = 150^\circ\text{C}$.
2. The EAS data shows Max. rating . The test condition is $V_{DD}=25\text{V}, V_{GS}=10\text{V}, L=0.4\text{mH}, I_{AS}=26\text{A}$.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics



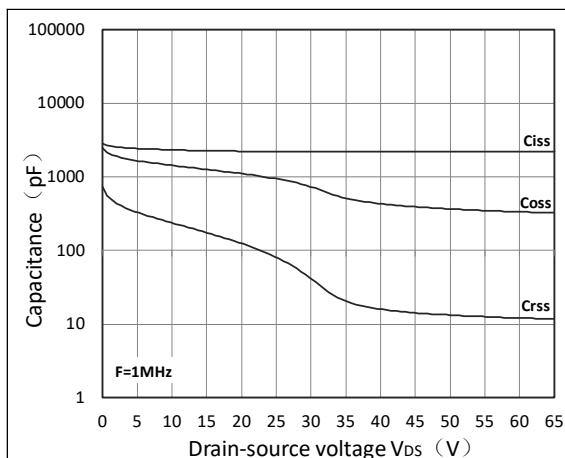
N-Ch 60V Fast Switching MOSFETs


Figure 7. Capacitance Characteristics

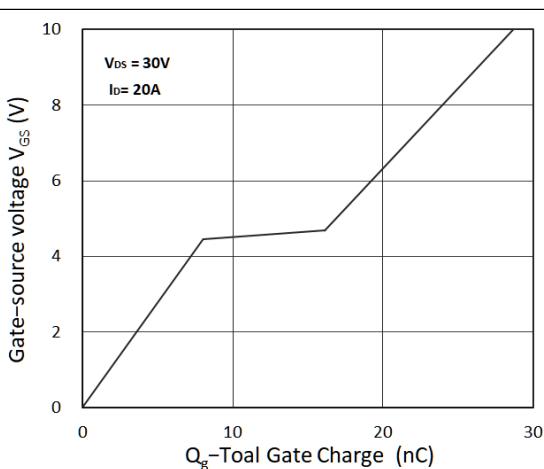


Figure 8. Gate Charge Characteristics

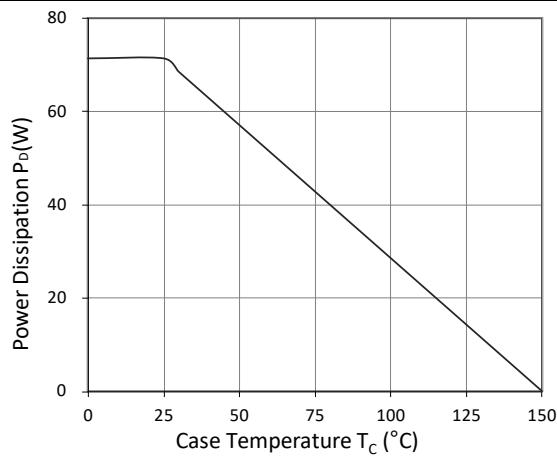


Figure 9. Power Dissipation

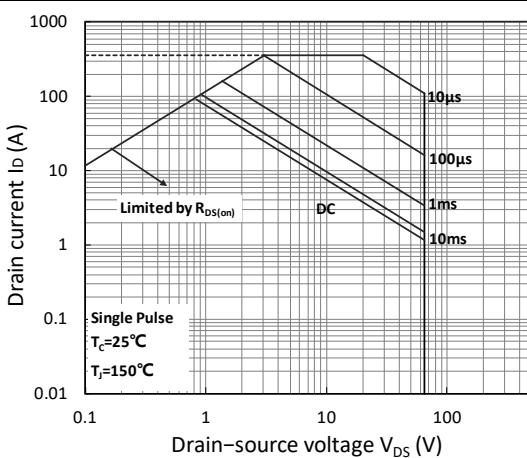


Figure 10. Safe Operating Area

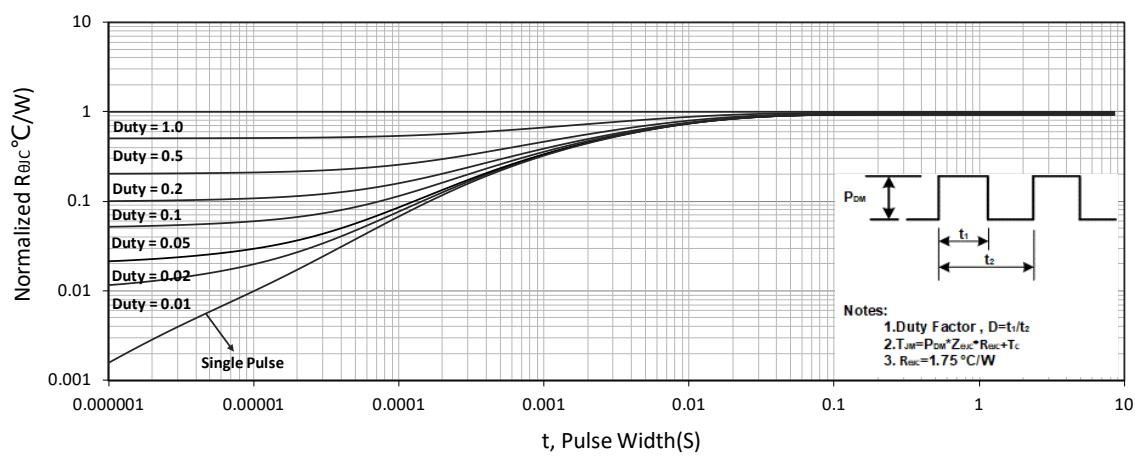
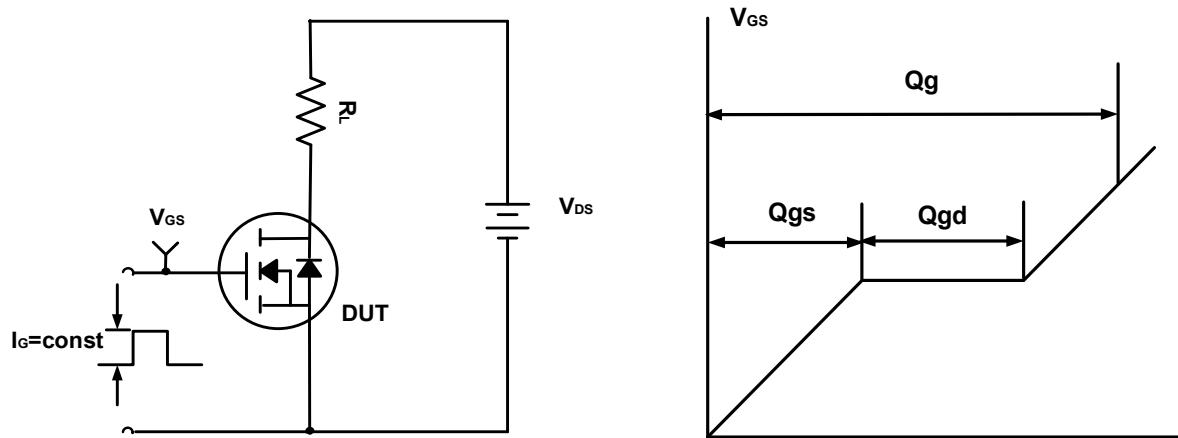
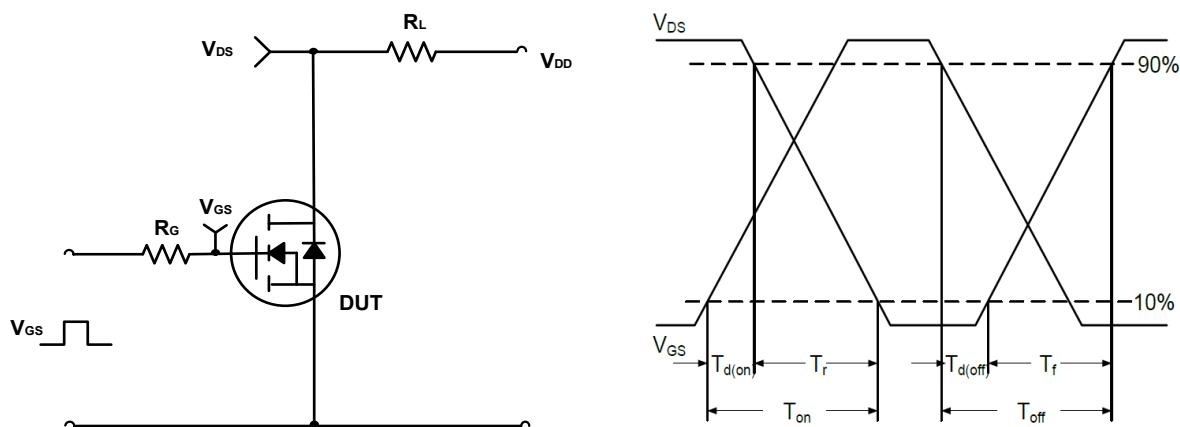
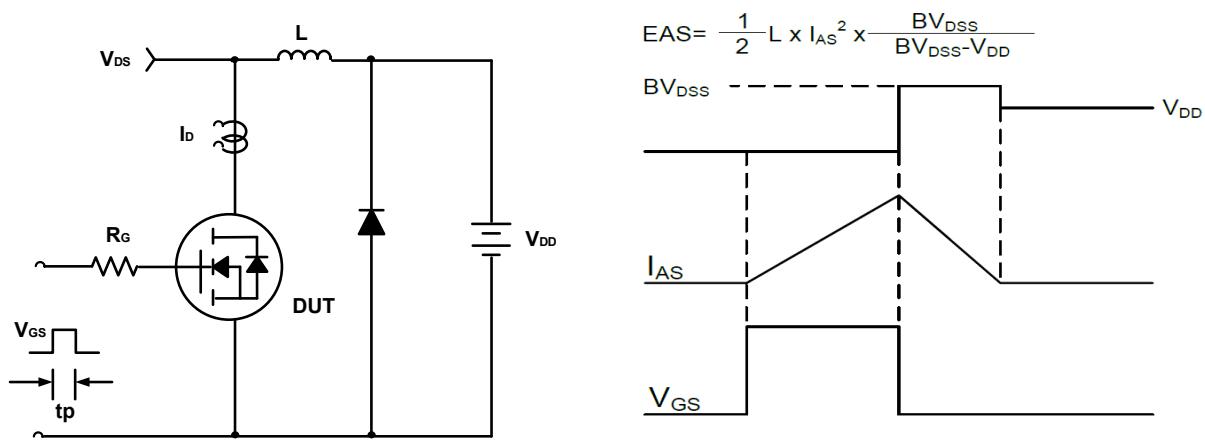
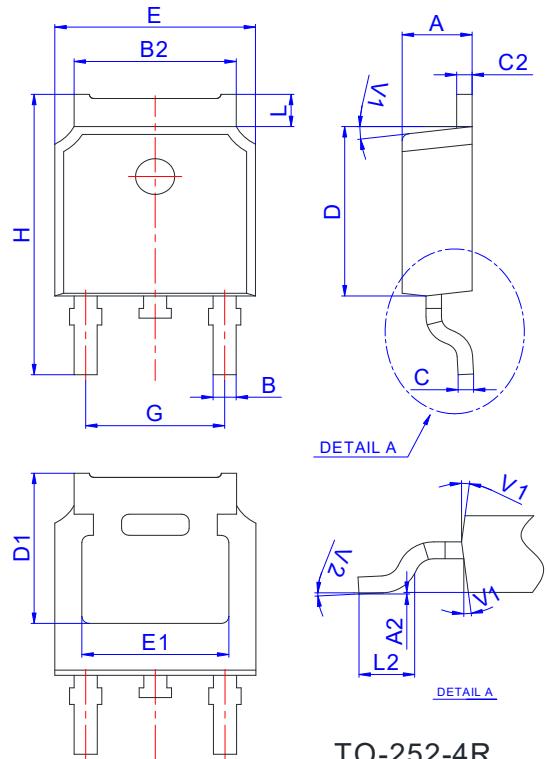


Figure 11. Normalized Maximum Transient Thermal Impedance

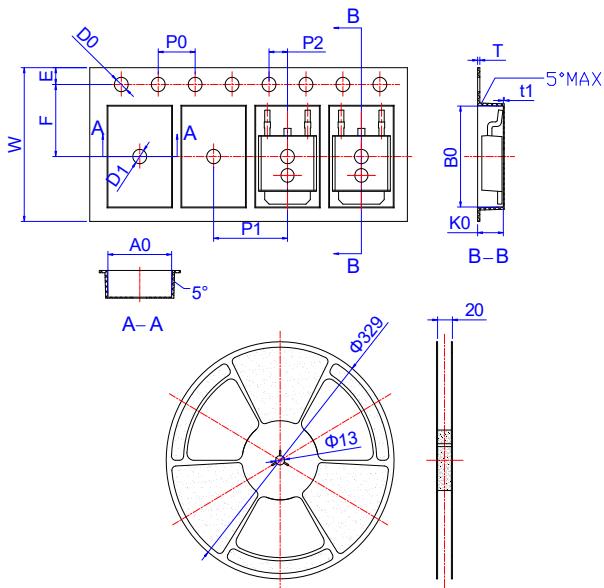
Test Circuit

Figure A. Gate Charge Test Circuit & Waveforms

Figure B. Switching Test Circuit & Waveforms

Figure C. Unclamped Inductive Switching Circuit & Waveforms

Package Mechanical Data-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583